

	Hit s	Search Text	DBs
18	28	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4)) and ((second near16 (expos\$4 or irradiat\$4 or illuminat\$4))) and pitch\$4 and linewidth and ((imprint\$4 or ion\$3beam or e\$2beam or (electron near4 beam)) near5 (system or apparatus or module)) and (diffract\$4 near26 grat\$4) and (beam near14 split\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
19	7	S18 NOT S16	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
20	0	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array) same pattern) and ((second or subsequent\$3 or sequential\$3) near16 (expos\$4 or irradiat\$4 or illuminat\$4) near26 (mask or reticle or photomask) near12 (second or different) near9 pattern) and pitch\$4 and linewidth and ((imprint\$4 or ion\$3beam or e\$2beam or (electron near4 beam)) near5 (system or apparatus or module)) and (diffract\$4 near26 grat\$4) and (beam near14 split\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
21	33	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array) same pattern) and ((second or subsequent\$3 or sequential\$3) near16 (expos\$4 or irradiat\$4 or illuminat\$4) near26 (mask or reticle or photomask) near12 (second or different) near9 pattern) and pitch\$4 and linewidth	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
22	25	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array or (diffract\$4 near9 grat\$4)) same pattern same (holograph\$4 or (interference near9 lithograph\$4))) and pitch\$4 and linewidth	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
23	0	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array or (diffract\$4 near9 grat\$4)) same pattern same holograph\$4 same (interfer\$6 near9 lithograph\$4)) and pitch\$4 and linewidth	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
24	0	((resist or photoresist) same (wafer or workpiece or substrate)) and ((first or initial) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array or (diffract\$4 near9 grat\$4)) same pattern same holograph\$4 same (interfer\$6 near9 lithograph\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
25	1	((resist or photoresist) same (wafer or workpiece or substrate)) and ((expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array or (diffract\$4 near9 grat\$4)) same pattern same holograph\$4 same (interfer\$6 near9 lithograph\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
26	4	((resist or photoresist) same (wafer or workpiece or substrate)) and ((expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array or (diffract\$4 near9 grat\$4)) same holograph\$4 same (interfer\$6 near9 lithograph\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
27	1	("5415835").PN.	US-PGPUB; USPAT

	Hit s	Search Text	DBs
28	14	((resist or photoresist) same (wafer or workpiece or substrate)) and ((resist or photoresist) same (first or initial or binary) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array or grating) same pattern) and ((second or subsequent\$3 or sequential\$3 or stepper or projection) near16 (expos\$4 or irradiat\$4 or illuminat\$4) near26 (mask or reticle or photomask) near12 ((second or different) near16 (pitch or pattern))) and pitch\$4 and linewidth and ("k" or rayleigh)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
29	14	((resist or photoresist) same (first or initial or binary) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array or grating) same pattern) and ((second or subsequent\$3 or sequential\$3 or stepper or projection) near16 (expos\$4 or irradiat\$4 or illuminat\$4) near26 (mask or reticle or photomask) near12 ((second or different) near16 (pitch or pattern))) and pitch\$4 and linewidth and ("k" or rayleigh)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
30	14	((resist or photoresist) same (first or initial or interference or holograph\$4) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array or grating)) and ((second or subsequent\$3 or sequential\$3 or stepper or projection or binary) near16 (expos\$4 or irradiat\$4 or illuminat\$4) near26 (mask or reticle or photomask) near12 ((second or different) near16 (pitch or pattern))) and pitch\$4 and linewidth and ("k" or rayleigh)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
31	20	((resist or photoresist) same (first or initial or interference or holograph\$4) same (expos\$4 or illuminat\$4 or irradiat\$4) same ((line near12 space) or array or grating)) and ((second or subsequent\$3 or sequential\$3 or stepper or projection or binary) same (expos\$4 or irradiat\$4 or illuminat\$4) same (mask or reticle or photomask) same ((second or different) near16 (pitch or pattern))) and pitch\$4 and linewidth and ("k" or rayleigh)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB